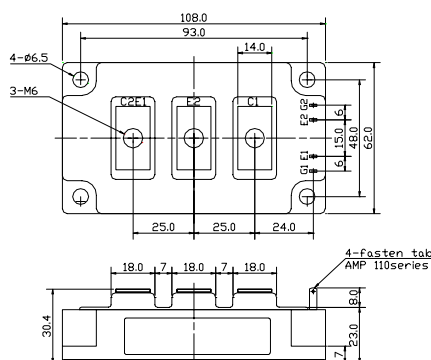
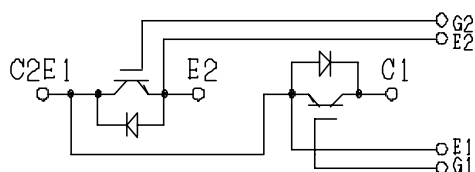


# IGBT MODULE Dual 150A 1200V

## PDMB150B12C

### CIRCUIT

### OUTLINE DRAWING



4-fasten- tab No 110

Dimension(mm)

Approximate Weight : 500g

### MAXMUM RATINGS (Tc=25°C)

| Item                                           |                           | Symbol           | PDMB150B12C | Unit |
|------------------------------------------------|---------------------------|------------------|-------------|------|
| Collector-Emitter Voltage                      |                           | V <sub>CES</sub> | 1200        | V    |
| Gate - Emitter Voltage                         |                           | V <sub>GES</sub> | +/- 20      | V    |
| Collector Current                              | DC                        | I <sub>C</sub>   | 150         | A    |
|                                                | 1 ms                      | I <sub>CP</sub>  | 300         |      |
| Collector Power Dissipation                    |                           | P <sub>C</sub>   | 730         | W    |
| Junction Temperature Range                     |                           | T <sub>j</sub>   | -40 to +150 | °C   |
| Storage Temperature Range                      |                           | T <sub>stg</sub> | -40 to +125 | °C   |
| Isolation Voltage Terminal to Base AC, 1 min.) |                           | V <sub>ISO</sub> | 2500        | V    |
| Mounting Torque                                | Module Base to Heatsink   | F <sub>TOR</sub> | 3           | N•m  |
|                                                | Bus Bar to Main Terminals |                  |             |      |

### ELECTRICAL CHARACTERISTICS (Tc=25°C)

| Characteristic                       |               | Symbol               | Test Condition                                    | Min. | Typ.  | Max. | Unit |
|--------------------------------------|---------------|----------------------|---------------------------------------------------|------|-------|------|------|
| Collector-Emitter Cut-Off Current    |               | I <sub>CES</sub>     | V <sub>CE</sub> =1200V, V <sub>GE</sub> =0V       | -    | -     | 3.0  | mA   |
| Gate-Emitter Leakage Current         |               | I <sub>GES</sub>     | V <sub>GE</sub> =+/- 20V, V <sub>CE</sub> =0V     | -    | -     | 1.0  | μA   |
| Collector-Emitter Saturation Voltage |               | V <sub>CE(sat)</sub> | I <sub>C</sub> =150A, V <sub>GE</sub> =15V        | -    | 1.9   | 2.4  | V    |
| Gate-Emitter Threshold Voltage       |               | V <sub>GE(th)</sub>  | V <sub>CE</sub> =5V, I <sub>C</sub> =150mA        | 4.0  | -     | 8.0  | V    |
| Input Capacitance                    |               | C <sub>ies</sub>     | V <sub>CE</sub> =10V, V <sub>GE</sub> =0V, f=1MHz | -    | 12600 | -    | pF   |
| Switching Time                       | Rise Time     | t <sub>r</sub>       | V <sub>CC</sub> = 600V                            | -    | 0.25  | 0.45 | μs   |
|                                      | Turn-on Time  | t <sub>on</sub>      | R <sub>L</sub> = 4 ohm                            | -    | 0.40  | 0.70 |      |
|                                      | Fall Time     | t <sub>f</sub>       | R <sub>G</sub> = 3.6 ohm                          | -    | 0.25  | 0.35 |      |
|                                      | Turn-off Time | t <sub>off</sub>     | V <sub>GE</sub> = +/- 15V                         | -    | 0.80  | 1.10 |      |

### FREE WHEELING DIODES RATINGS & CHARACTERISTICS (Tc=25°C)

| Item            |      | Symbol          | Rated Value | Unit |
|-----------------|------|-----------------|-------------|------|
| Forward Current | DC   | I <sub>F</sub>  | 150         | A    |
|                 | 1 ms | I <sub>FM</sub> | 300         |      |

| Characteristic        | Symbol          | Test Condition                                             | Min. | Typ. | Max. | Unit |
|-----------------------|-----------------|------------------------------------------------------------|------|------|------|------|
| Peak Forward Voltage  | V <sub>F</sub>  | I <sub>F</sub> =150A, V <sub>GE</sub> =0V                  | -    | 1.9  | 2.4  | V    |
| Reverse Recovery Time | t <sub>rr</sub> | I <sub>F</sub> =150A, V <sub>GE</sub> =-10V, di/dt=300A/μs | -    | 0.2  | 0.3  | μs   |

### THERMAL CHARACTERISTICS

| Characteristic    |       | Symbol               | Test Condition   | Min. | Typ. | Max. | Unit |
|-------------------|-------|----------------------|------------------|------|------|------|------|
| Thermal Impedance | IGBT  | R <sub>th(j-c)</sub> | Junction to Case | -    | -    | 0.16 | °C/W |
|                   | DIODE |                      |                  | -    | -    | 0.32 |      |

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Fig.1- Output Characteristics (Typical)

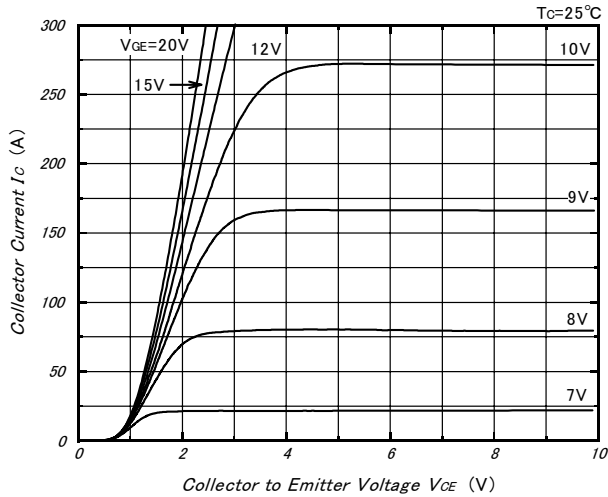


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

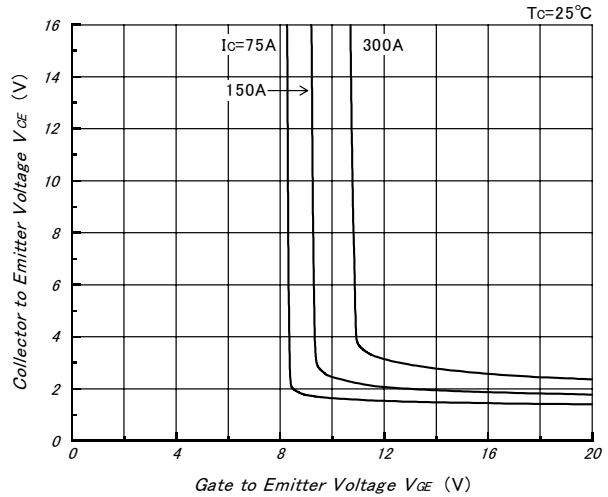


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

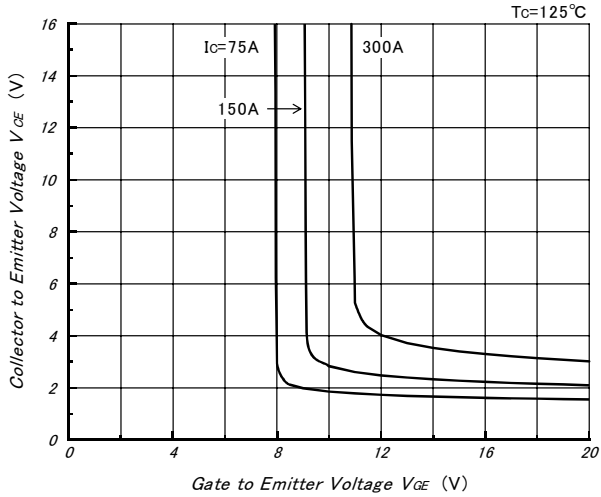


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

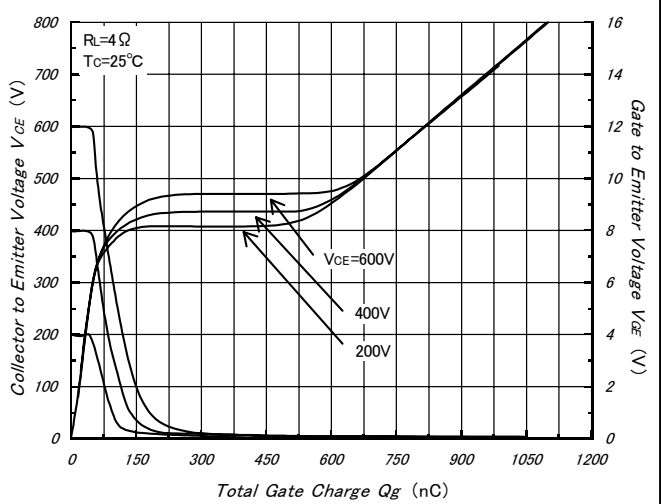


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

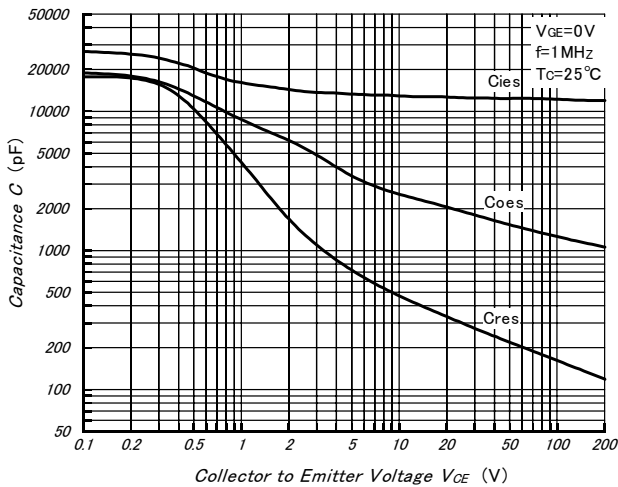
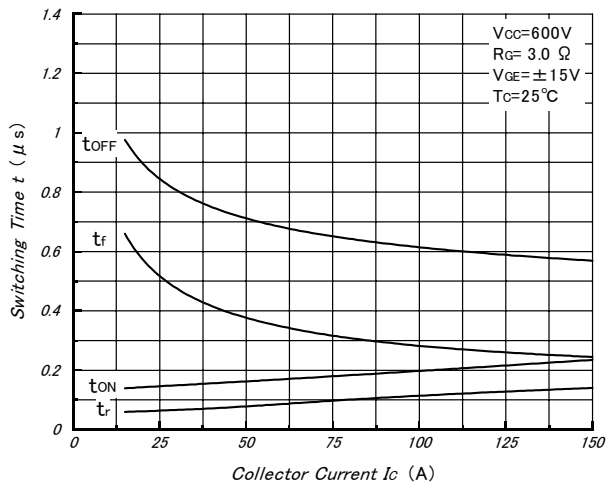


Fig.6- Collector Current vs. Switching Time (Typical)



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Fig.7- Series Gate Impedance vs. Switching Time (Typical)

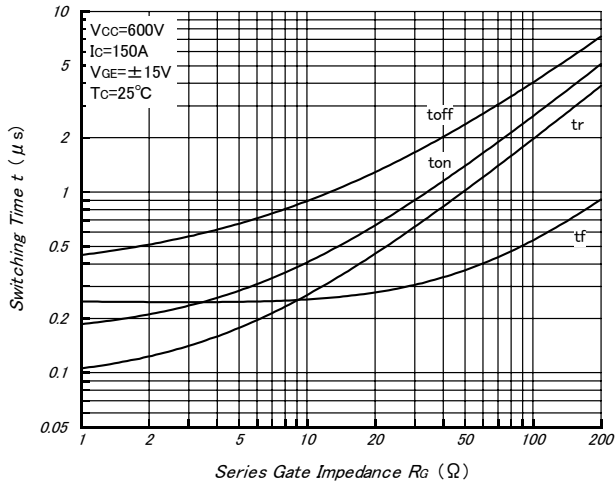


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

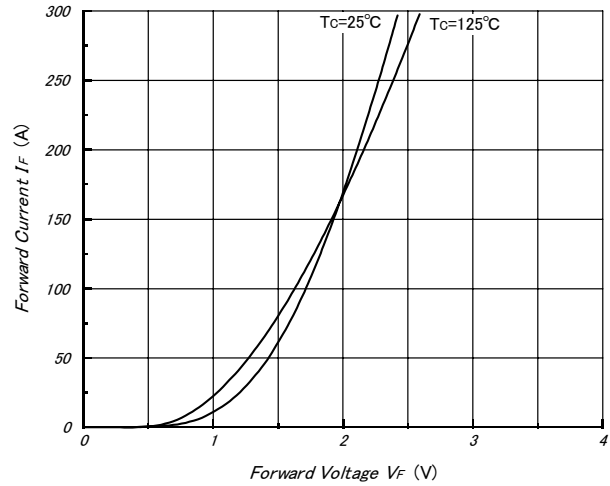


Fig.9- Reverse Recovery Characteristics (Typical)

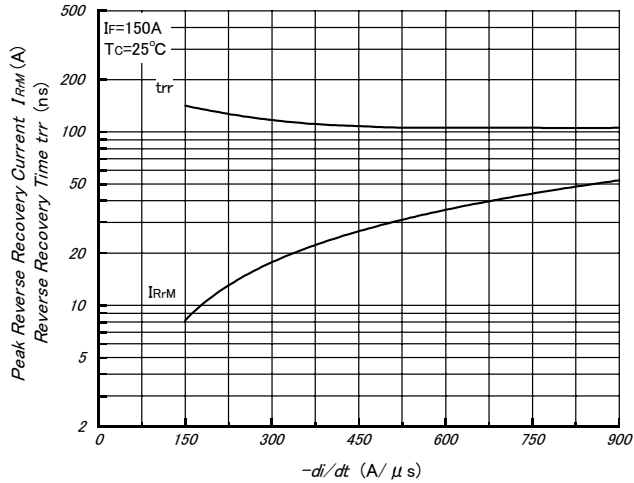


Fig.10- Reverse Bias Safe Operating Area (Typical)

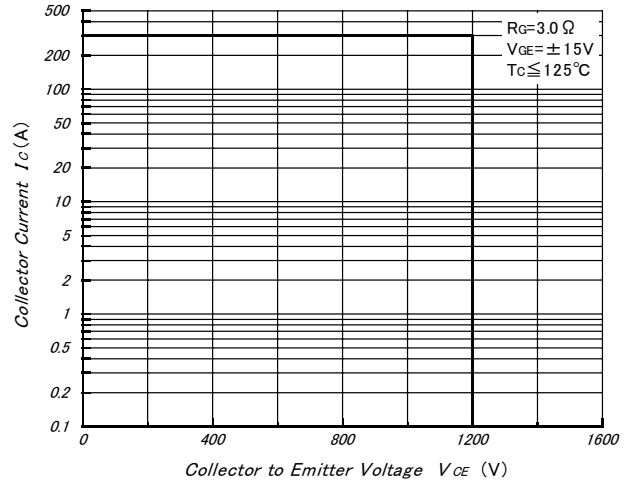


Fig.11- Transient Thermal Impedance

